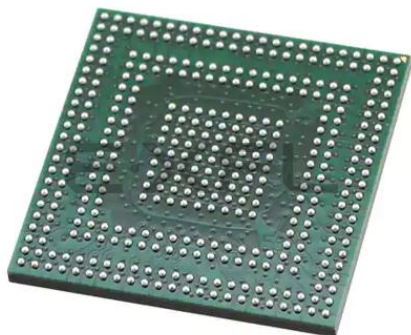


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Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Last Time Buy
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	369-LFBGA
Supplier Device Package	369-PBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8306vmafdca

1 Overview

The MPC8306 incorporates the e300c3 (MPC603e-based) core built on Power Architecture® technology, which includes 16 Kbytes of each L1 instruction and data caches, dual integer units, and on-chip memory management units (MMUs). The MPC8306 also includes two DMA engines and a 16-bit DDR2 memory controller.

A new communications complex based on QUICC Engine technology forms the heart of the networking capability of the MPC8306. The QUICC Engine block contains several peripheral controllers and a 32-bit RISC controller. Protocol support is provided by the main workhorses of the device—the unified communication controllers (UCCs). A block diagram of the MPC8306 is shown in the following figure.

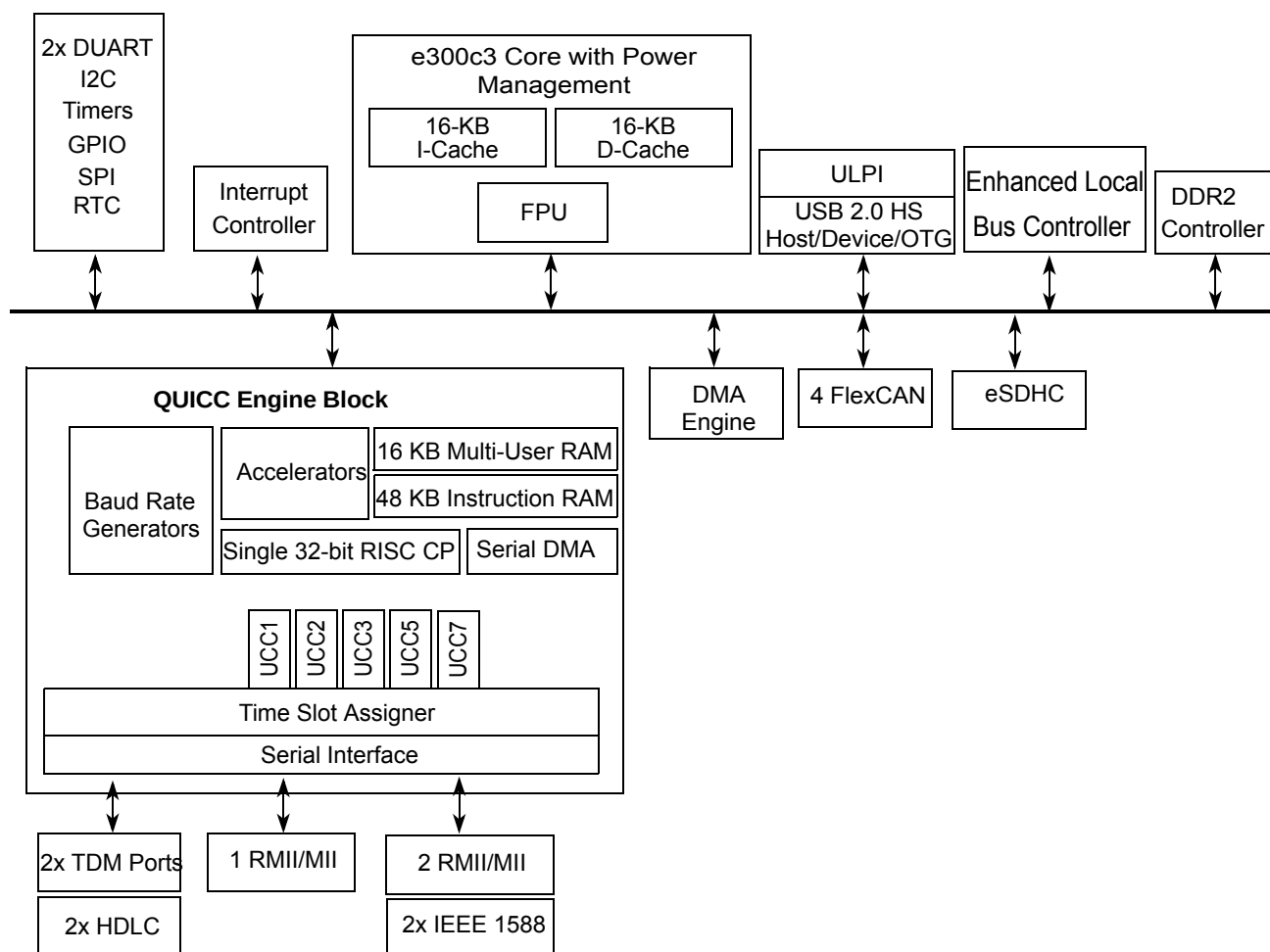


Figure 1. MPC8306 Block Diagram

Each of the five UCCs can support a variety of communication protocols such as 10/100 Mbps MII/RMII Ethernet, IEEE-1588, HDLC and TDM.

- Asynchronous HDLC (bit rate up to 2 Mbps)
- Two TDM interfaces supporting up to 128 QUICC multichannel controller channels, each running at 64 kbps

For more information on QUICC Engine sub-modules, see *QUICC Engine Block Reference Manual with Protocol Interworking*.

- DDR SDRAM memory controller
 - Programmable timing supporting DDR2 SDRAM
 - Integrated SDRAM clock generation
 - 16-bit data interface, up to 266-MHz data rate
 - 14 address lines
 - The following SDRAM configurations are supported:
 - Up to two physical banks (chip selects), 256-Mbyte per chip select for 16 bit data interface.
 - 64-Mbit to 2-Gbit devices with x8/x16 data ports (no direct x4 support)
 - One 16-bit device or two 8-bit devices on a 16-bit bus,
 - Support for up to 16 simultaneous open pages for DDR2
 - One clock pair to support up to 4 DRAM devices
 - Supports auto refresh
 - On-the-fly power management using CKE
- Enhanced local bus controller (eLBC)
 - Multiplexed 26-bit address and 8-/16-bit data operating at up to 66 MHz
 - Eight chip selects supporting eight external slaves
 - Four chip selects dedicated
 - Four chip selects offered as multiplexed option
 - Supports boot from parallel NOR Flash and parallel NAND Flash
 - Supports programmable clock ratio dividers
 - Up to eight-beat burst transfers
 - 16- and 8-bit ports, separate $\overline{\text{LWE}}$ for each 8 bit
 - Three protocol engines available on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user programmable machines (UPMs)
 - NAND Flash control machine (FCM)
 - Variable memory block sizes for FCM, GPCM, and UPM mode
 - Default boot ROM chip select with configurable bus width (8 or 16)
 - Provides two Write Enable signals to allow single byte write access to external 16-bit eLBC slave devices
- Integrated programmable interrupt controller (IPIC)
 - Functional and programming compatibility with the MPC8260 interrupt controller
 - Support for external and internal discrete interrupt sources

2.1.2 Power Supply Voltage Specification

The following table provides the recommended operating conditions for the MPC8306. Note that these values are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Note
Core supply voltage	V_{DD}	$1.0 \text{ V} \pm 50 \text{ mV}$	V	1
PLL supply voltage	AV_{DD1} AV_{DD2} AV_{DD3}	$1.0 \text{ V} \pm 50 \text{ mV}$	V	1
DDR2 DRAM I/O voltage	GV_{DD}	$1.8 \text{ V} \pm 100 \text{ mV}$	V	1
Local bus, DUART, system control and power management, I ² C, SPI, MII, RMII, MII management, eSDHC, FlexCAN, USB and JTAG I/O voltage	OV_{DD}	$3.3 \text{ V} \pm 300 \text{ mV}$	V	1, 3
Junction temperature	T_A/T_J	0 to 105	°C	2

Notes:

- GV_{DD} , OV_{DD} , AV_{DD} , and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
- Minimum temperature is specified with T_A (Ambient Temperature); maximum temperature is specified with T_J (Junction Temperature).
- OV_{DD} here refers to $NVDDA$, $NVddb$, $NVDDC$, $NVDDF$, $NVDDG$, and $NVDDH$ from the ball map.

The following figure shows the undershoot and overshoot voltages at the interfaces of the MPC8306

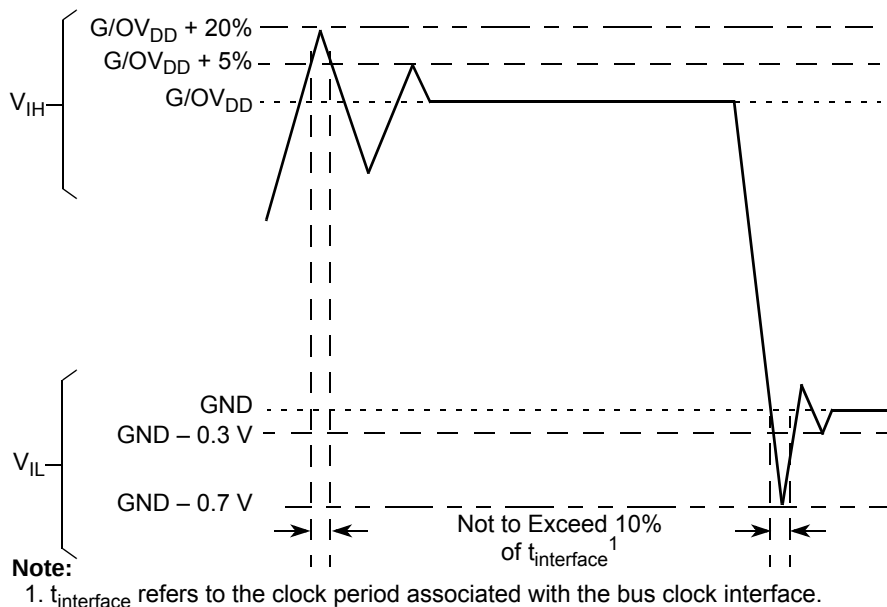


Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/OV_{DD}

The following table shows the estimated typical I/O power dissipation for the device.

Table 6. Typical I/O Power Dissipation

Interface	Parameter	GV _{DD} (1.8 V)	OV _{DD} (3.3 V)	Unit	Comments
DDR I/O 65% utilization 1.8 V R _s = 20 Ω R _t = 50 Ω 1 pair of clocks	266 MHz, 1 × 16 bits	0.141	—	W	—
Local bus I/O load = 25 pF 1 pair of clocks	66 MHz, 26 bits	—	0.150	W	1
QUICC Engine block and other I/Os	TDM serial, HDLC/TRAN serial, DUART, MII, RMII, Ethernet management, USB, SPI, Timer output, FlexCAN, eSDHC				

Note:

1. Typical I/O power is based on a nominal voltage of V_{DD} = 3.3V, ambient temperature, and the core running a Dhrystone benchmark application. The measurements were taken on the evaluation board using WC process silicon.

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the MPC8306.

NOTE

The rise/fall time on QUICC Engine input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of OV_{DD}; fall time refers to transitions from 90% to 10% of OV_{DD}.

4.1 DC Electrical Characteristics

The following table provides the clock input (SYS_CLK_IN) DC specifications for the MPC8306. These specifications are also applicable for QE_CLK_IN.

Table 7. SYS_CLK_IN DC Electrical Characteristics

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V _{IH}	2.4	OV _{DD} + 0.3	V
Input low voltage	—	V _{IL}	−0.3	0.4	V
SYS_CLK_IN input current	0 V ≤ V _{IN} ≤ OV _{DD}	I _{IN}	—	±5	μA
SYS_CLK_IN input current	0 V ≤ V _{IN} ≤ 0.5 V or OV _{DD} − 0.5 V ≤ V _{IN} ≤ OV _{DD}	I _{IN}	—	±5	μA
SYS_CLK_IN input current	0.5 V ≤ V _{IN} ≤ OV _{DD} − 0.5 V	I _{IN}	—	±50	μA

Table 16. DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of $1.8V \pm 100mV$.

Parameter	Symbol ¹	Min	Max	Unit	Note
MCS output hold with respect to MCK 266 MHz	t_{DDKHCX}	2.5	—	ns	3
MCK to MDQS Skew	t_{DDKMHM}	−0.6	0.6	ns	4
MDQ/MDM output setup with respect to MDQS 266 MHz	t_{DDKHDS} , t_{DDKLDS}	0.9	—	ns	5
MDQ/MDM output hold with respect to MDQS 266 MHz	t_{DDKHDX} , t_{DDKLDX}	1100	—	ps	5
MDQS preamble start	t_{DDKHMP}	$0.75 \times t_{MCK}$	—	ns	6
MDQS epilogue end	t_{DDKHME}	$0.4 \times t_{MCK}$	$0.6 \times t_{MCK}$	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/MCK referenced measurements are made from the crossing of the two signals $\pm 0.1\ V$.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the Clock Control register is set to adjust the memory clocks by 1/2 applied cycle.
4. Note that t_{DDKMHM} follows the symbol conventions described in note 1. For example, t_{DDKMHM} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKMHM} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjusts in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8306 PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. t_{DDKHMP} follows the symbol conventions described in note 1.

Table 19. MII and RMII DC Electrical Characteristics

Parameter	Symbol	Conditions	Min	Max	Unit
Supply voltage 3.3 V	OV_{DD}	—	3	3.6	V
Output high voltage	V_{OH}	$I_{OH} = -4.0 \text{ mA}$ $OV_{DD} = \text{Min}$	2.40	$OV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 4.0 \text{ mA}$ $OV_{DD} = \text{Min}$	GND	0.50	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.90	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA

8.2 MII and RMII AC Timing Specifications

The AC timing specifications for MII and RMII are presented in this section.

8.2.1 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.1.1 MII Transmit AC Timing Specifications

The following table provides the MII transmit AC timing specifications.

Table 20. MII Transmit AC Timing Specifications

At recommended operating conditions with OV_{DD} of $3.3 \text{ V} \pm 300\text{mV}$.

Parameter/Condition	Symbol ¹	Min	Typical	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise $V_{IL}(\text{max})$ to $V_{IH}(\text{min})$	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall $V_{IH}(\text{min})$ to $V_{IL}(\text{max})$	t_{MTXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

12 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8306.

12.1 DUART DC Electrical Characteristics

The following table provides the DC electrical characteristics for the DUART interface of the MPC8306.

Table 34. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage OV_{DD}	V_{IL}	-0.3	0.8	V
High-level output voltage, $I_{OH} = -100 \mu A$	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100 \mu A$	V_{OL}	—	0.2	V
Input current ($0 V \leq V_{IN} \leq OV_{DD}$) ¹	I_{IN}	—	± 5	μA

Note:

- Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

12.2 DUART AC Electrical Specifications

The following table provides the AC timing parameters for the DUART interface of the MPC8306.

Table 35. DUART AC Timing Specifications

Parameter	Value	Unit	Note
Minimum baud rate	256	baud	—
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

Notes:

- Actual attainable baud rate is limited by the latency of interrupt processing.
- The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

Table 41. I²C AC Electrical Specifications (continued)

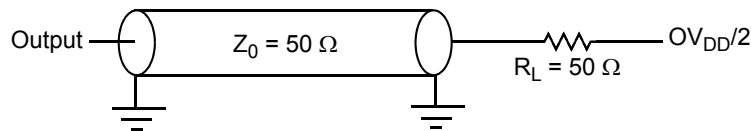
All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 40).

Parameter	Symbol ¹	Min	Max	Unit
Fall time of both SDA and SCL signals	t_{I2CF}	$20 + 0.1 C_B^4$	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μ s
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μ s
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

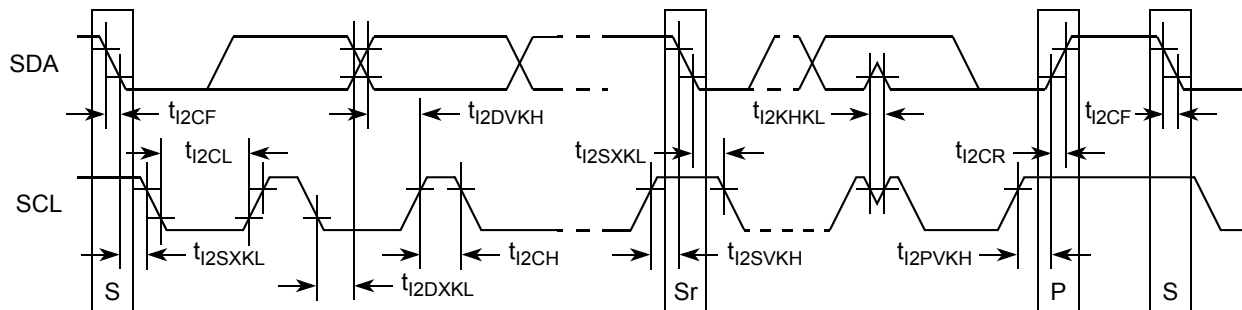
Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. MPC8306 provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH} (min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKL} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

The following figure provides the AC test load for the I²C.


Figure 29. I²C AC Test Load

The following figure shows the AC timing diagram for the I²C bus.


Figure 30. I²C Bus AC Timing Diagram

16 Timers

This section describes the DC and AC electrical specifications for the timers of the MPC8306.

16.1 Timer DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306 timer pins, including $\overline{\text{TIN}}$, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_PIT_CLK .

Table 42. Timer DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -6.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 6.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA

16.2 Timer AC Timing Specifications

The following table provides the timer input and output AC timing specifications.

Table 43. Timer Input AC Timing Specifications¹

Characteristic	Symbol ²	Min	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:

- Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLK_IN . Timings are measured at the pin.
- Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by any external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

The following figure provides the AC test load for the timers.

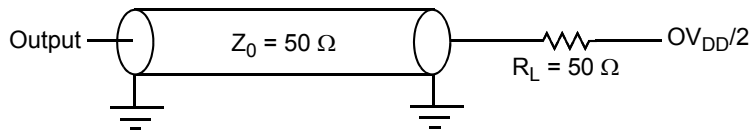


Figure 31. Timers AC Test Load

17 GPIO

This section describes the DC and AC electrical specifications for the GPIO of the MPC8306.

17.1 GPIO DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306 GPIO.

Table 44. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Output high voltage	V_{OH}	$I_{OH} = -6.0 \text{ mA}$	2.4	—	V	1
Output low voltage	V_{OL}	$I_{OL} = 6.0 \text{ mA}$	—	0.5	V	1
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V	1
Input low voltage	V_{IL}	—	-0.3	0.8	V	—
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA	—

Note:

1. This specification applies when operating from 3.3-V supply.

17.2 GPIO AC Timing Specifications

The following table provides the GPIO input and output AC timing specifications.

Table 45. GPIO Input AC Timing Specifications¹

Characteristic	Symbol ²	Min	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLK_IN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

The following figure provides the AC test load for the GPIO.

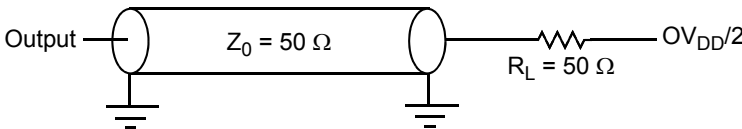


Figure 32. GPIO AC Test Load

18 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8306.

18.1 IPIC DC Electrical Characteristics

The following table provides the DC electrical characteristics for the external interrupt pins of the MPC8306.

Table 46. IPIC DC Electrical Characteristics^{1,2}

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	—	—	± 5	μA
Output High Voltage	V_{OH}	$I_{OL} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 6.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

Notes:

1. This table applies for pins $\overline{IRQ}$, $\overline{MCP_OUT}$, and QE ports Interrupts.
2. $\overline{MCP_OUT}$ is open drain pins, thus V_{OH} is not relevant for those pins.

18.2 IPIC AC Timing Specifications

The following table provides the IPIC input and output AC timing specifications.

Table 47. IPIC Input AC Timing Specifications¹

Characteristic	Symbol ²	Min	Unit
IPIC inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLK_IN . Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by any external synchronous logic. IPIC inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation when working in edge triggered mode.

19 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8306.

19.1 SPI DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306 SPI.

Table 51. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)¹ (continued)

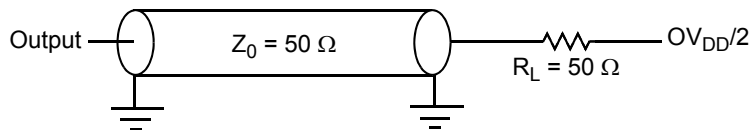
At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
Output hold times: Boundary-scan data TDO	t_{JTKLDX} t_{JTKLOX}	2 2	— —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	t_{JTKLDZ} t_{JTKLOZ}	2 2	19 9	ns	5, 6 6

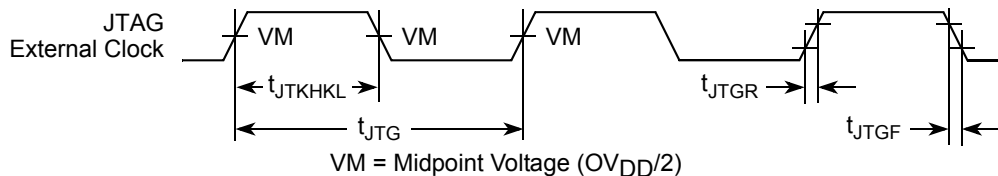
Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 36). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{JTDVXH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDVXH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{TRST}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK} .
5. Non-JTAG signal output timing with respect to t_{TCLK} .
6. Guaranteed by design and characterization.

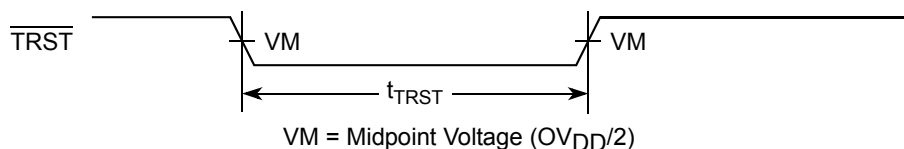
The following figure provides the AC test load for TDO and the boundary-scan outputs of the MPC8306.


Figure 36. AC Test Load for the JTAG Interface

The following figure provides the JTAG clock input timing diagram.


Figure 37. JTAG Clock Input Timing Diagram

The following figure provides the $\overline{TRST}$ timing diagram.


Figure 38. $\overline{TRST}$ Timing Diagram

21 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8306 is available in a thermally enhanced MAPBGA (mold array process-ball grid array); see [Section 21.1, “Package Parameters for the MPC8306,”](#) and [Section 21.2, “Mechanical Dimensions of the MPC8306 MAPBGA,”](#) for information on the MAPBGA.

21.1 Package Parameters for the MPC8306

The package parameters are as provided in the following list.

Package outline	19 mm × 19 mm
Package Type	MAPBGA
Interconnects	369
Pitch	0.80 mm
Module height (typical)	1.48 mm; Min = 1.31mm and Max 1.61mm
Solder Balls	96 Sn / 3.5 Ag / 0.5 Cu (VM package)
Ball diameter (typical)	0.40 mm

21.2 Mechanical Dimensions of the MPC8306 MAPBGA

The following figure shows the mechanical dimensions and bottom surface nomenclature of the MPC8306, 369-MAPBGA package.

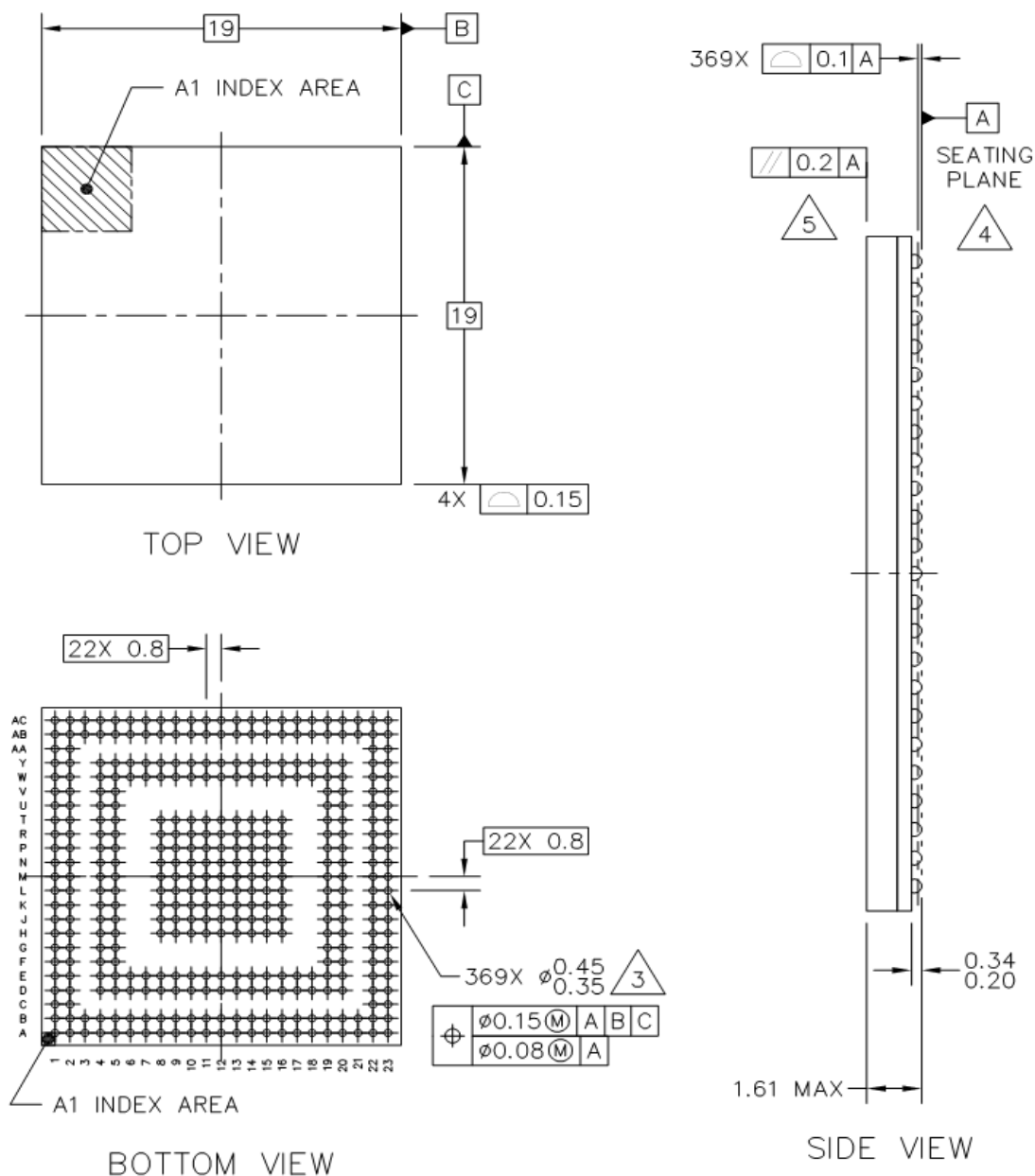


Figure 41. Mechanical Dimensions and Bottom Surface Nomenclature of the MPC8306 MAPBGA

Notes:

1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Table 52. MPC8306 Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
FEC1_TX_ER/GTM1_TOUT[4]_B/GPIO[27]	AC17	IO	OV _{DD}	—
FEC1_TXD0/GTM1_TOUT[1]_B/GPIO[28]	AB16	IO	OV _{DD}	—
FEC1_TXD1/GTM1_TOUT[2]_B/GPIO[29]	AC16	IO	OV _{DD}	—
FEC1_TXD2/GTM1_TOUT[3]_B/GPIO[30]	AC15	IO	OV _{DD}	—
FEC1_TXD3/GPIO[31]	AB14	IO	OV _{DD}	—
FEC2/GPIO				
FEC2_COL/GPIO[32]	AC14	IO	OV _{DD}	—
FEC2_CRS/GPIO[33]	AB13	IO	OV _{DD}	—
FEC2_RX_CLK/GPIO[34]	Y14	IO	OV _{DD}	—
FEC2_RX_DV/GPIO[35]	AC13	IO	OV _{DD}	—
FEC2_RX_ER/GPIO[36]	Y13	IO	OV _{DD}	—
FEC2_RXD0/GPIO[37]	AC12	IO	OV _{DD}	—
FEC2_RXD1/GPIO[38]	AB11	IO	OV _{DD}	—
FEC2_RXD2/GPIO[39]	AC11	IO	OV _{DD}	—
FEC2_RXD3/GPIO[40]	AB10	IO	OV _{DD}	—
FEC2_TX_CLK/GPIO[41]	Y12	IO	OV _{DD}	—
FEC2_TX_EN/GPIO[42]	AC10	IO	OV _{DD}	—
FEC2_TX_ER/GPIO[43]	AC9	IO	OV _{DD}	—
FEC2_TXD0/GPIO[44]	AC8	IO	OV _{DD}	—
FEC2_TXD1/GPIO[45]	Y11	IO	OV _{DD}	—
FEC2_TXD2/GPIO[46]	AC7	IO	OV _{DD}	—
FEC2_TXD3/GPIO[47]	Y10	IO	OV _{DD}	—
FEC3/GPIO				
FEC3_COL/GPIO[48]	J23	IO	OV _{DD}	—
FEC3_CRS/GPIO[49]	K23	IO	OV _{DD}	—
FEC3_RX_CLK/GPIO[50]	M20	IO	OV _{DD}	—
FEC3_RX_DV/GPIO[51]	K22	IO	OV _{DD}	—
FEC3_RX_ER/GPIO[52]	L22	IO	OV _{DD}	—
FEC3_RXD0/GPIO[53]	L23	IO	OV _{DD}	—
FEC3_RXD1/GPIO[54]	M23	IO	OV _{DD}	—
FEC3_RXD2/FEC_TMR_TRIG1/GPIO[55]	N22	IO	OV _{DD}	—
FEC3_RXD3/FEC_TMR_TRIG2/GPIO[56]	N23	IO	OV _{DD}	—
FEC3_TX_CLK/FEC_TMR_CLK/GPIO[57]	N20	IO	OV _{DD}	—
FEC3_TX_EN/FEC_TMR_GCLK/GPIO[58]	P20	IO	OV _{DD}	—
FEC3_TX_ER/FEC_TMR_PP1/GPIO[59]	P22	IO	OV _{DD}	—

Table 52. MPC8306 Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
FEC3_TXD0/FEC_TMR_PP2/GPIO[60]	R20	IO	OV _{DD}	—
FEC3_TXD1/FEC_TMR_PP3/GPIO[61]	T22	IO	OV _{DD}	—
FEC3_TXD2/FEC_TMR_ALARM1/GPIO[62]	T23	IO	OV _{DD}	—
FEC3_TXD3/FEC_TMR_ALARM2/GPIO[63]	T20	IO	OV _{DD}	—
HDLC/GPIO/TDM				
HDLC1_RXCLK/TDM1_RCK/GPIO[1]	U23	IO	OV _{DD}	—
HDLC1_RXD/TDM1_RD/GPIO[3]	U22	IO	OV _{DD}	—
HDLC1_TXCLK/GPIO[0]/TDM1_TCK/ QE_BRG[5]	AC22	IO	OV _{DD}	—
HDLC1_TXD/GPIO[2]/TDM1_TD/ CFG_RESET_SOURCE[0]	W18	IO	OV _{DD}	—
HDLC1_CD_B/GPIO[4]/TDM1_TFS	W19	IO	OV _{DD}	—
HDLC1_CTS_B/GPIO[5]/TDM1_RFS	Y20	IO	OV _{DD}	—
HDLC1_RTS_B/GPIO[6]/TDM1_STROBE_B/ CFG_RESET_SOURCE[1]	AB22	IO	OV _{DD}	—
HDLC2_TXCLK/GPIO[16]/TDM2_TCK/ QE_BRG[7]	AB23	IO	OV _{DD}	—
HDLC2_RXCLK/GPIO[17]/TDM2_RCK/ QE_BRG[8]	AA23	IO	OV _{DD}	—
HDLC2_TXD/GPIO[18]/TDM2_TD/ CFG_RESET_SOURCE[2]	W20	IO	OV _{DD}	—
HDLC2_RXD/GPIO[19]/TDM2_RD	Y23	IO	OV _{DD}	—
HDLC2_CD_B/GPIO[20]/TDM2_TFS	Y22	IO	OV _{DD}	—
HDLC2_CTS_B/GPIO[21]/TDM2_RFS	W23	IO	OV _{DD}	—
HDLC2_RTS_B/GPIO[22]/TDM2_STROBE_B/ CFG_RESET_SOURCE[3]	W22	IO	OV _{DD}	—
Power				
AV _{DD1}	L16	—	—	—
AV _{DD2}	M16	—	—	—
AV _{DD3}	N8	—	—	—
GV _{DD}	G5, H5, J5, K5, L5, M5, N5, P5, R5, T5, U5	—	—	—
OV _{DD}	E7,E8,E9,E10,E11,E12, E13,E14, E15, E16,E17,G19,H19,J19,K 19,L19,M19, N19,P19,R19,T19,U19, W7,W8,W9, W10,W11, W12,W13, W14,W15, W16, W17	—	—	—

Table 52. MPC8306 Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
V _{DD}	H8,H9,H10,H11,H12,H13,H14,H15,H16,J8,J16,K8,K16,M8,N16,P8,P16,R8,R16,T8,T9,T10,T11,T12,T13,T14,T15,T16	—	—	—
VSS	A1,B4,B6,B9,B12,B15,B18,B21,C22,D2,D5,D18,D20,F2,F22,J2,J9,J10,J11,J12,J13,J14,J15,J22,K4,K9,K10,K11,K12,K13,K14,K15,L9,L10,L11,L12,L13,L14,L15,M2,M9,M10,M11,M12,M13,M14,M15,M22,N9,N10,N11,N12,N13,N14,N15,P9,P10,P11,P12,P13,P14,P15,R2,R9,R10,R11,R12,R13,R14,R15,R22,T4,V2,V19,V22,W4,Y19,AA2,AA22,AB4,AB6,AB9,AB12,AB15,AB18,AB21,AC1,AC23	—	—	—
NC	A23	—	—	—
Notes 1. This pin is an open drain signal. A weak pull-up resistor (1 kΩ) should be placed on this pin to OV _{DD} 2. This pin is an open drain signal. A weak pull-up resistor (2-10 kΩ) should be placed on this pin to OV _{DD} 3. This pin has weak pull-up that is always enabled.				

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

23.1.3 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D) \quad \text{Eqn. 2}$$

where:

T_J = junction temperature (°C)

T_B = board temperature at the package perimeter (°C)

$R_{\theta JB}$ = junction-to-board thermal resistance (°C/W) per JESD51-8

P_D = power dissipation in package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

23.1.4 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the thermal characterization parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D) \quad \text{Eqn. 3}$$

where:

T_J = junction temperature (°C)

24.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins. The voltage level at each AV_{DDn} pin should always be equivalent to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide independent filter circuits as illustrated in Figure 44, one to each of the three AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

The following figure shows the PLL power supply filter circuit.

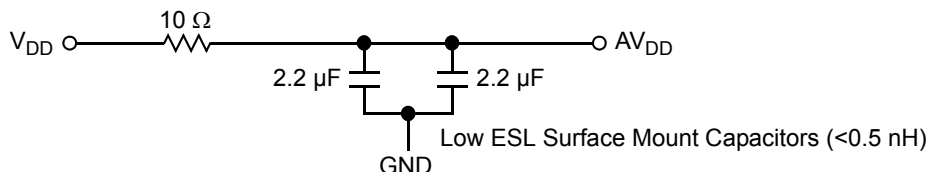


Figure 44. PLL Power Supply Filter Circuit

24.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the MPC8306 can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8306 system, and MPC8306 itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD} , OV_{DD} , and GV_{DD} pins of the MPC8306. These decoupling capacitors should receive their power from separate V_{DD} , OV_{DD} , GV_{DD} , and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 μF . Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD} , OV_{DD} , and GV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias

to minimize inductance. Suggested bulk capacitors—100 to 330 μF (AVX TPS tantalum or Sanyo OSCON).

24.4 Output Buffer DC Impedance

For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $\text{OV}_{\text{DD}}/2$ (see Figure 45). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $\text{OV}_{\text{DD}}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

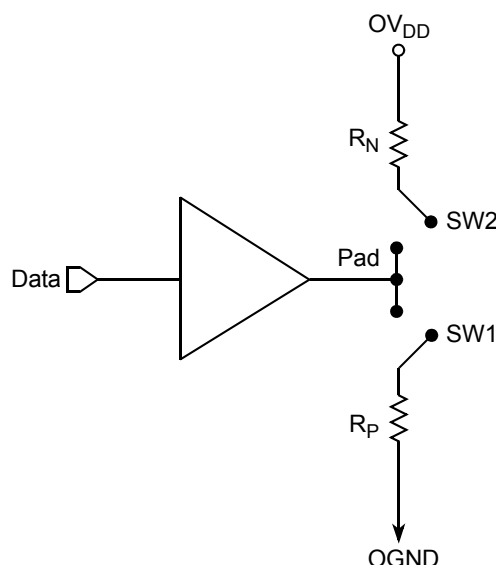


Figure 45. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{\text{source}} \times I_{\text{source}}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{\text{source}}$. Solving for the output impedance gives $R_{\text{source}} = R_{\text{term}} \times (V_1/V_2 - 1)$. The drive current is then $I_{\text{source}} = V_1/R_{\text{source}}$.